TRF37D73 1-6000MHz 射频 (RF) 增益块

1 特性

- 1MHz-6000MHz
- 增益：19.5dB
- 噪声值：3.25dB
- 输出 P1dB：2000MHz 时为 16.5dBm
- 输出 IP3：2000MHz 时为 28dBm
- 节电模式
- 单电源：3.3V
- 温度范围内的稳定性能
- 无条件稳定
- 强健的静电放电 (ESD) 防护：> 1kV 人体模型 (HBM)；> 1kV 充电器件模型 (CDM)

2 应用范围

- 通用 RF 增益块
- 消费类产品
- 工业用
- 公用事业计量仪表
- 低成本无线电产品
- 蜂窝基站
- 无线基础设施
- RF 回程
- 雷达
- 电子对抗
- 软件定义的无线电
- 测试和测量
- 点对点/多点微波
- 软件定义的无线电
- RF 中继器
- 分布式天线系统
- 本振 (LO) 和 PA 驱动器放大器
- 无线数据，卫星，直播卫星 (DBS)，有线电视 (CATV)
- 中频 (IF) 放大器

3 说明

TRF37D73 采用具有节电引脚的 2.00mm x 2.00mm 超薄小外形尺寸无引线 (WSON) 封装，这使得这款器件非常适合于空间占用和低功率模式十分关键的应用。

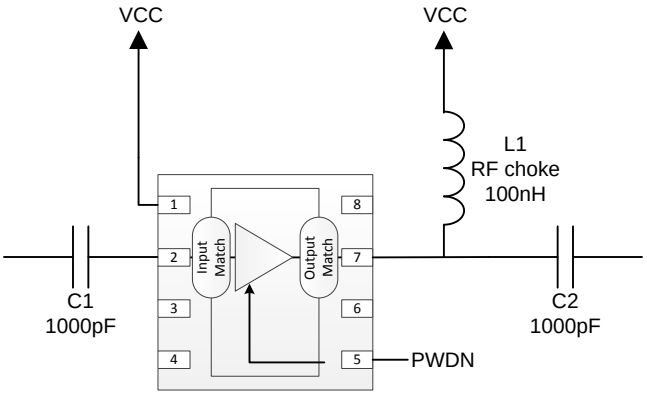
TRF37D73 的设计目的是易于使用。 为了实现最大灵活性，这个产品系列使用常见的 3.3V 电源，并且流耗为 53mA。 此外，这一系列在设计时使用了有源偏置电路，此电路在过程、温度和电压变化范围内提供一个稳定且可预计的偏置电流。 为了实现增益和线性预算，此器件被设计成提供一个平坦增益响应，以及频率达到 6000MHz 时的出色 OIP3 输出。 针对空间受限应用，这一系列与 50Ω 内部匹配，这样简化了使用，并且最大限度地减小了所需的印刷电路板 (PCB) 面积。

器件信息(1)

产品型号	封装	封装尺寸（标称值）
TRF37D73	WSON (32)	2.00mm x 2.00mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

简化电路原理图



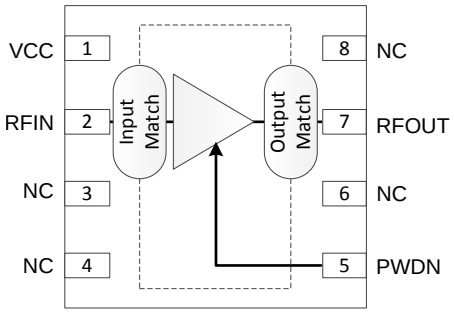
目录

4 修订历史记录

日期	修订版本	注释
2014 年 5 月	*	最初发布。

5 Pin Configuration and Functions

DSG PACKAGE
(TOP VIEW)



Pin Functions

PIN		DESCRIPTION
NAME	NO.	
VCC	1	DC Bias.
RFIN	2	RF input. Connect to an RF source through a DC-blocking capacitor. Internally matched to 50 Ω.
NC	3, 4, 6, 8	No electrical connection. Connect pad to GND for board level reliability integrity.
PWDN	5	When high the device is in power down state. When LOW or NC the device is in active state. Internal pulldown resistor to GND.
RFOUT	7	RF Output and DC Bias (V_{CC}). Connect to DC supply through an RF choke inductor. Connect to output load through a DC-blocking capacitor. Internally matched to 50 Ω.
GND	PowerPAD™	RF and DC GND. Connect to PCB ground plane.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

	MIN	MAX	UNIT
Supply Input voltage	–0.3	3.6	V
Input Power		10	dBm
Operating virtual junction temperature range	–40	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 Handling Ratings

			MIN	MAX	UNIT
T_{STG}	Storage temperature range		–65	150	°C
V_{ESD}	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	–1	1	kV
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	–1	1	kV

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
Supply Voltage, V_{CC}	3	3.3	3.45	V
Operating junction temperature, T_J	–40		125	°C

6.4 Thermal Information

THERMAL METRIC (1)		DSG	UNIT
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	79.3	°C/W
$R_{\theta JCtop}$	Junction-to-case (top) thermal resistance	110	
$R_{\theta JB}$	Junction-to-board thermal resistance	49	
ψ_{JT}	Junction-to-top characterization parameter	6	
ψ_{JB}	Junction-to-board characterization parameter	49.4	
$R_{\theta JCbot}$	Junction-to-case (bottom) thermal resistance	19.2	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

6.5 Electrical Characteristics

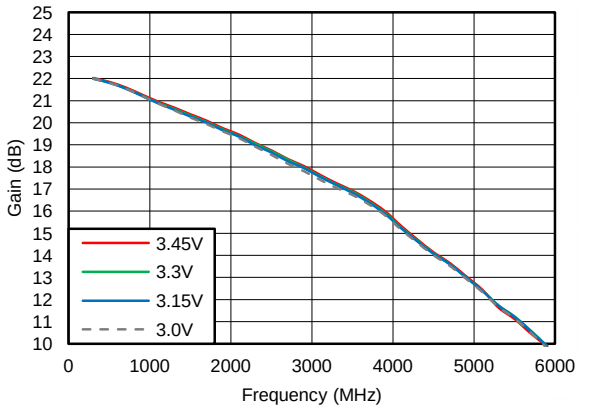
V_{CC} = 3V3, T_A = 25°C, PWDN = Low, L_{OUT} = 100 nH, C1 = C2 = 1000 pF, Z_S = Z_L = 50 Ω (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC PARAMETERS						
I_{CC}	Total supply current			53	65	mA
	Power down current	PWDN = High		125		µA
P_{diss}	Power dissipation			0.175		W
RF REQUENCY RANGE						
	Frequency range		1		6000	MHz
G	Small signal gain	f_{RF} = 400 MHz		22		dB
		f_{RF} = 2000 MHz		19.5		dB
		f_{RF} = 3000 MHz		18		dB
		f_{RF} = 4000 MHz		15.5		dB
		f_{RF} = 5000 MHz		13		dB
		f_{RF} = 6000 MHz		10		dB
OP1dB	Output 1dB compression point	At 2000 MHz		16.5		dBm
OIP3	Output 3rd order intercept point	At 2000 MHz, 2-tone 10 MHz apart		27.5		dBm
NF	Noise figure	At 2000 MHz		3.25		dB
$R_{(LI)}$	Input return loss	At 2000 MHz		20		dB
$R_{(LO)}$	Output return loss	At 2000 MHz		12		dB
PWDN PIN						
V_{IH}	High level input level		2			V
V_{IL}	Low level input level				0.8	V
I_{IH}	High level input current			30		µA
I_{IL}	Low level input current			1		µA

6.6 Timing Requirements

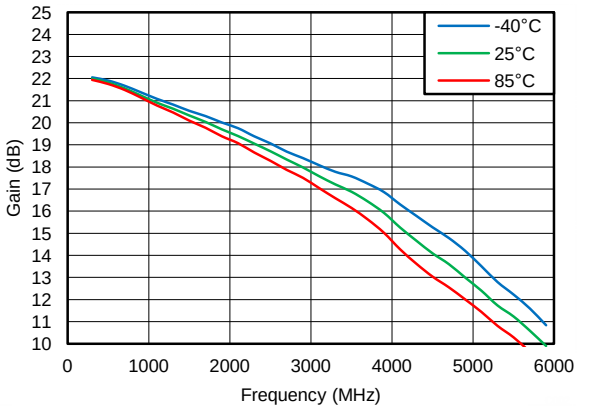
			MIN	TYP	MAX	UNIT
PWDN PIN						
t_{ON}	Turn-on Time	50% TTL to 90% P_{OUT}		0.6		µs
t_{OFF}	Turn-off Time	50% TTL to 10% P_{OUT}		1.4		µs

6.7 Typical Characteristics



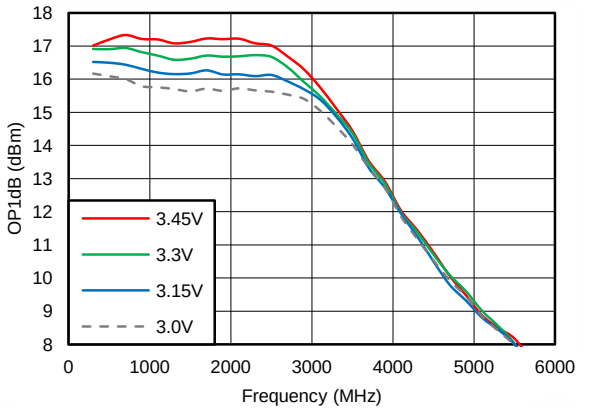
V_{CC} curves Temp = 25°C Pin = –10 dBm

Figure 1. Gain vs Frequency



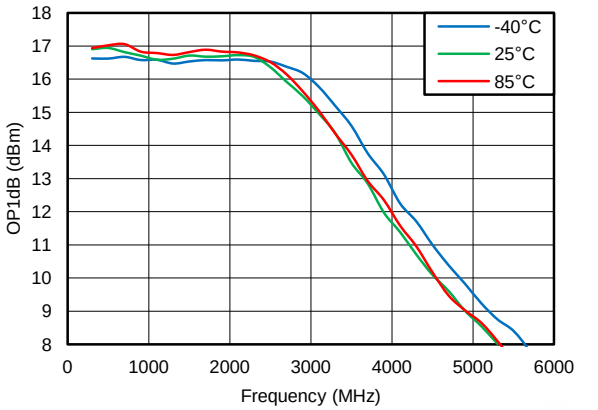
Temp curves V_{CC} = 3.3 V Pin = –10 dBm

Figure 2. Gain vs Frequency



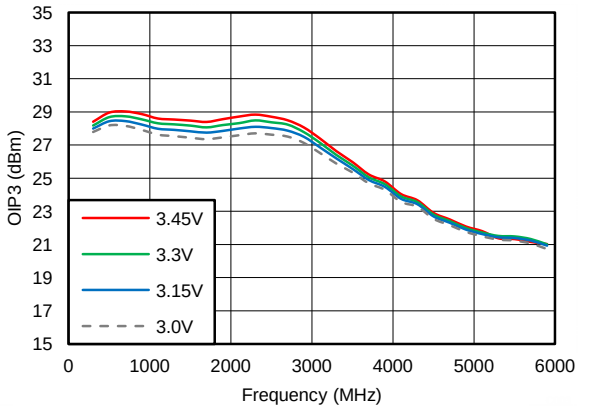
V_{CC} curves Temp = 25°C

Figure 3. OP1dB vs Frequency



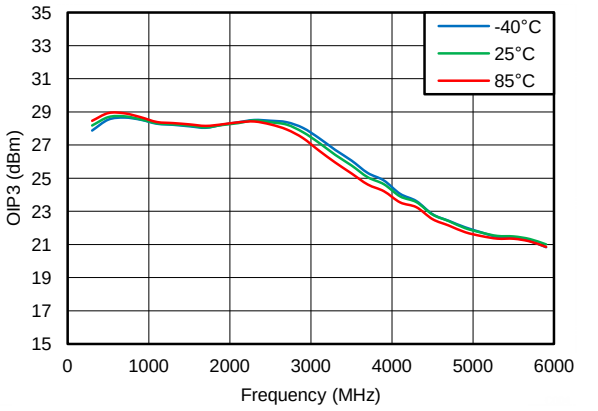
Temp curves V_{CC} = 3.3 V

Figure 4. OP1dB vs Frequency



V_{CC} curves Temp = 25°C Pin = –10 dBm/tone

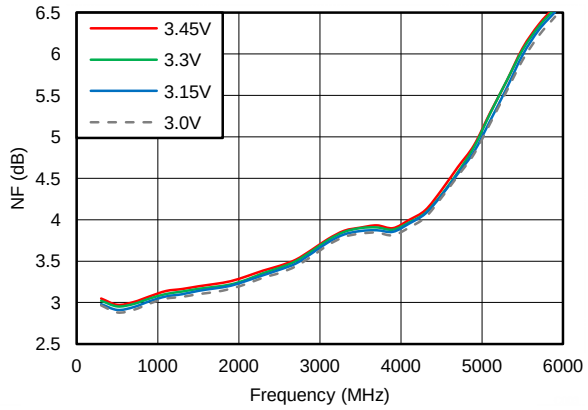
Figure 5. OIP3 vs Frequency



Temp curves V_{CC} = 3.3 V Pin = –10 dBm/tone

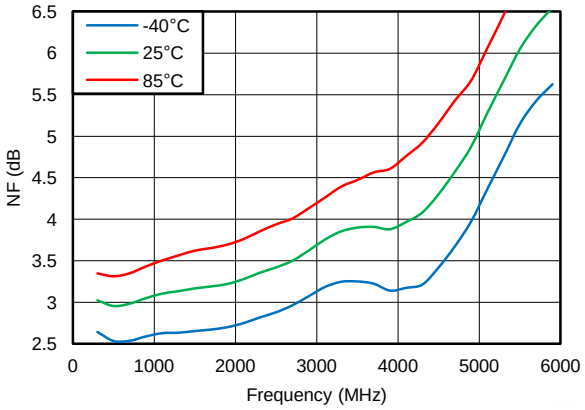
Figure 6. OIP3 vs Frequency

Typical Characteristics (continued)



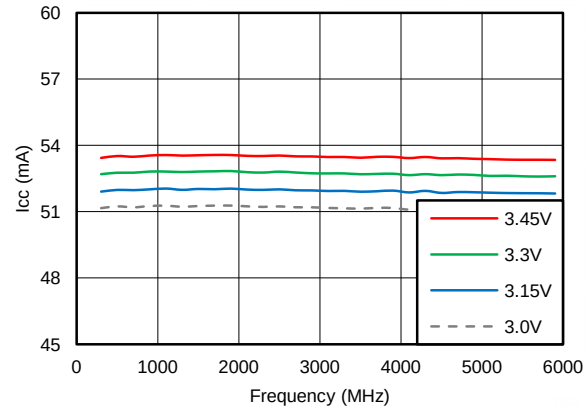
V_{CC} curves Temp = 25°C

Figure 7. NF vs Frequency



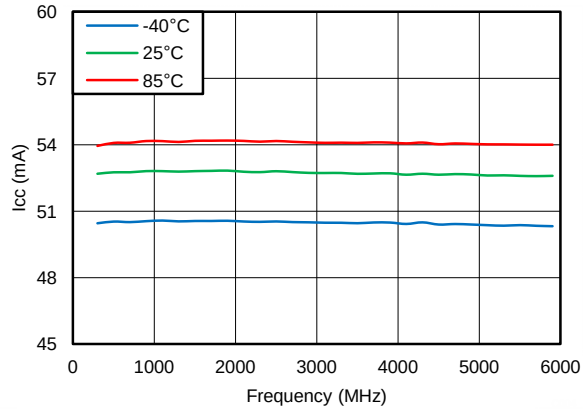
Temp curves V_{CC} = 3.3 V

Figure 8. NF vs Frequency



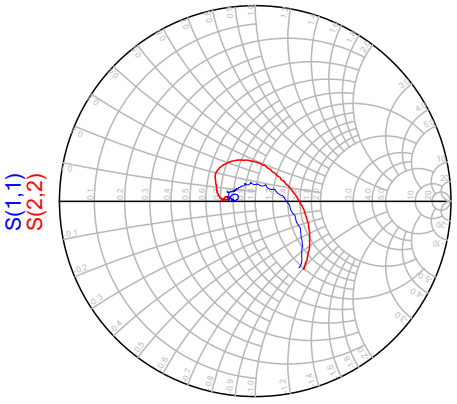
V_{CC} curves Temp = 25°C

Figure 9. I_{CC} vs Frequency



Temp curves V_{CC} = 3.3 V

Figure 10. I_{CC} vs Frequency

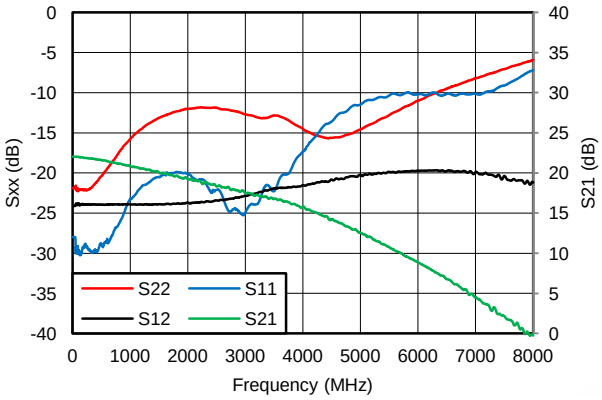


freq (1.000MHz to 8.000GHz)

V_{CC} = 3.3 V Temp = 25°C 1 MHz to 8 GHz

Data Taken with EVM and Bias T, De-embedded to DUT pin

Figure 11. Smith Chart – S11, S22



V_{CC} = 3.3 V Temp = 25°C 1 MHz to 8 GHz

Data Taken with EVM and Bias T, De-embedded to DUT pin

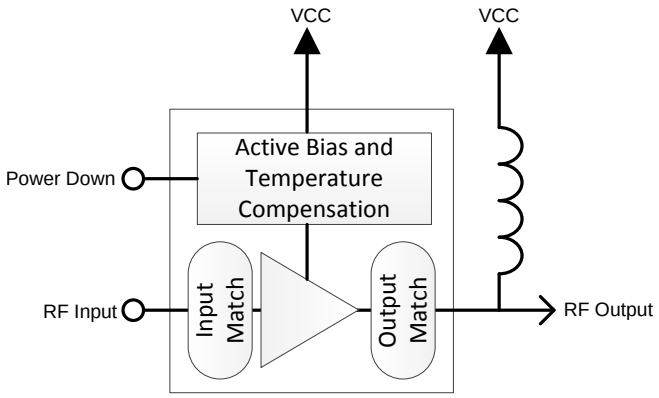
Figure 12. S22, S11, S12, S21

7 Detailed Description

7.1 Overview

The device is a 3.3 V general purpose RF gain block. It is a SiGe Darlington amplifier with integrated 50 Ω input and output matching. The device contains an active bias circuit to maintain performance over a wide temperature and voltage range. The included power down function allows the amplifier to shut down saving power when the amplifier is not needed. Fast shut down and start up enable the amplifier to be used in a host of time division duplex applications.

7.2 Functional Block Diagram



7.3 Feature Description

The TRF37D73 is a fixed gain RF amplifier. It is internally matched to 50 Ω on both the input and output. It is a fully cascadable general purpose amplifier. The included active bias circuitry ensures the amplifier performance is optimized over the full operating temperature and voltage ranges.

7.4 Device Functional Modes

7.4.1 Power Down

The TRF37D73 PWDN pin can be left unconnected for normal operation or a logic-high for disable mode operation. For applications that use the power down mode, normal 5 V TLL levels are supported.

8 Applications and Implementation

8.1 Application Information

The TRF37D73 is a wideband, high performance, general purpose RF amplifier. To maximize its performance, good RF layout and grounding techniques should be employed.

8.2 Typical Application

The TRF37D73 device is typically placed in a system as illustrated in Figure 13.

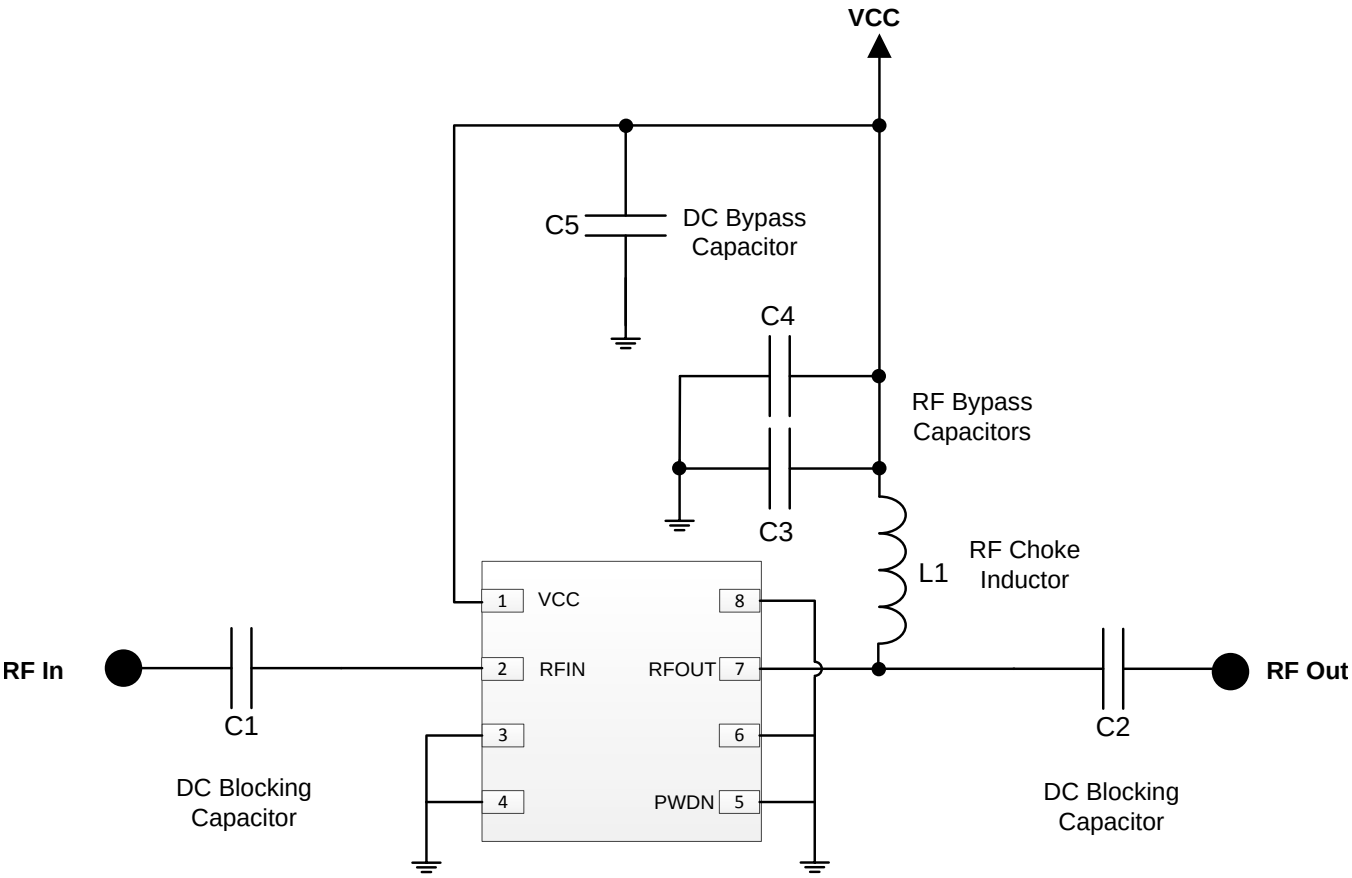


Figure 13. Typical Application Schematic for TRF37D73

8.2.1 Design Requirements

Table 1. Design Parameters

PARAMETERS	EXAMPLE VALUES
Input power range	< 3 dBm
Output power	< 18 dBm
Operating frequency range	1 — 6000 MHz

8.2.2 Detailed Design Procedure

The TRF37D73 is a simple to use internally matched and cascadable RF amplifier. Following the recommended RF layout with good quality RF components and local DC bypass capacitors will ensure optimal performance is achieved. TI provides various support materials including S-Parameter and ADS models to allow the design to be optimized to the user's particular performance needs.

8.2.3 Application Curve

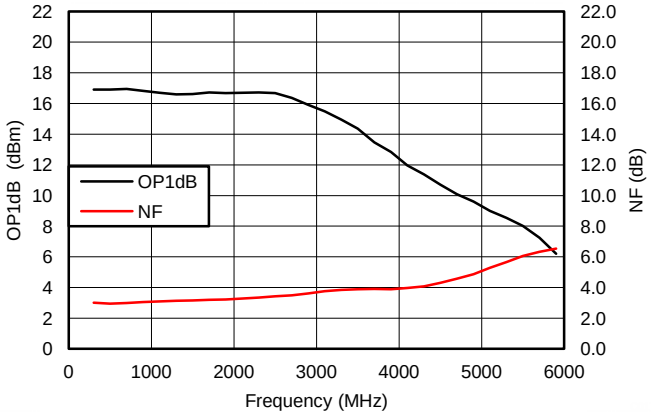


Figure 14. OP1dB and NF vs Frequency

9 Power Supply Recommendations

All supplies may be generated from a common nominal 3.3 V source but should be isolated through decoupling capacitors placed close to the device. The typical application schematic in Figure 13 is an excellent example. Select capacitors with self-resonant frequency near the application frequency. When multiple capacitors are used in parallel to create a broadband decoupling network, place the capacitor with the higher self-resonant frequency closer to the device. Expensive tantalum capacitors are not needed for optimal performance.

10 Layout

10.1 Layout Guidelines

Good layout practice helps to enable excellent linearity and isolation performance. An example of good layout is shown in Figure 15. In the example, only the top signal layer and its adjacent ground reference plane are shown.

- Excellent electrical connection from the PowerPAD™ to the board ground is essential. Use the recommended footprint, solder the pad to the board, and do not include solder mask under the pad.
- Connect pad ground to device terminal ground on the top board layer.
- Verify that the return DC and RF current path have a low impedance ground plane directly under the package and RF signal traces into and out of the amplifier.
- Ensure that ground planes on the top and any internal layers are well stitched with vias.
- Do not route RF signal lines over breaks in the reference ground plane.
- Avoid routing clocks and digital control lines near RF signal lines.
- Do not route RF or DC signal lines over noisy power planes. Ground is the best reference, although clean power planes can serve where necessary.
- Place supply decoupling close to the device.

10.2 Layout Example

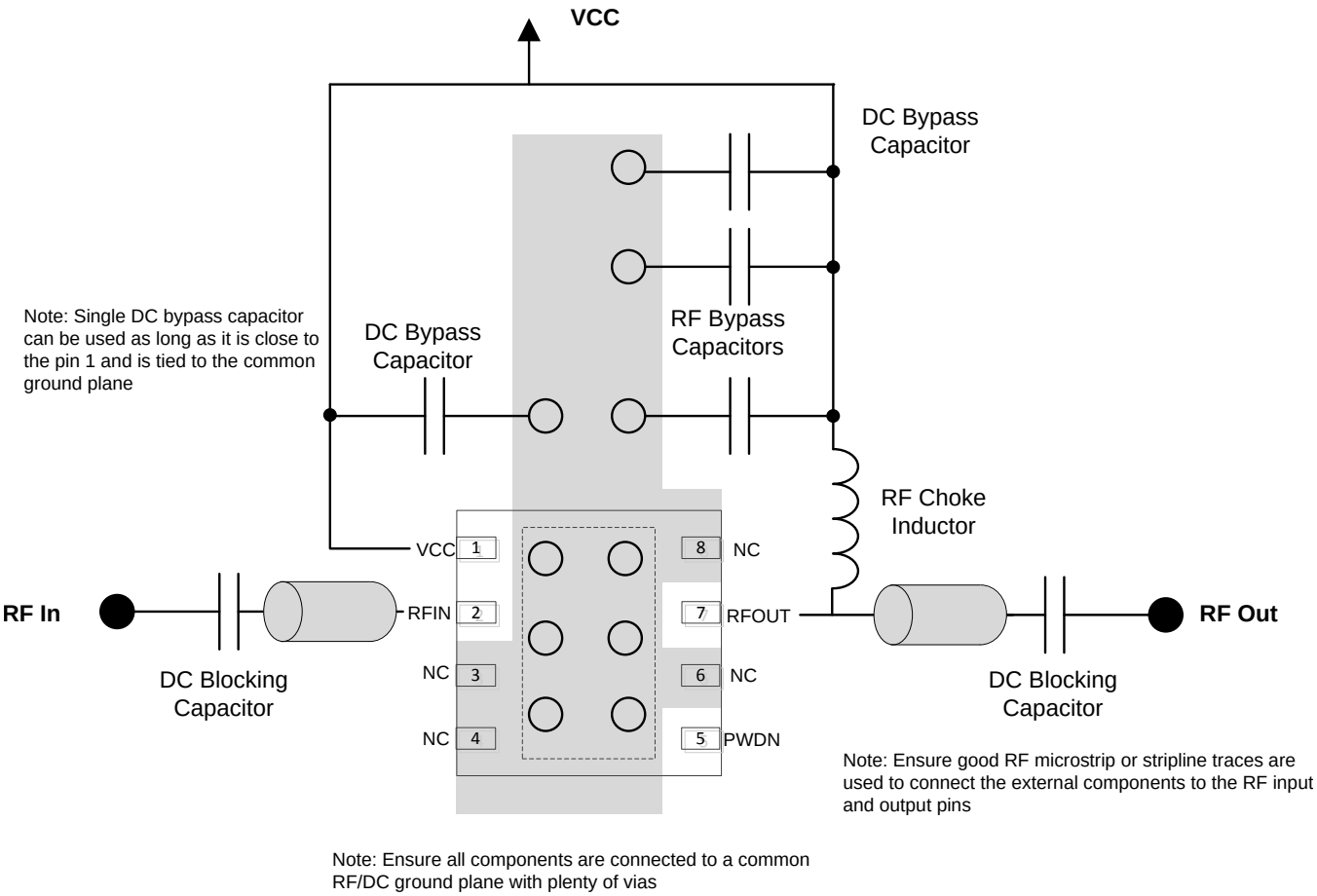


Figure 15. Layout

11 器件和文档支持

11.1 Trademarks

PowerPAD is a trademark of Texas Instruments.

11.2 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.3 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms and definitions.

12 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TRF37D73IDSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	D73I	Samples
TRF37D73IDSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	D73I	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

GENERIC PACKAGE VIEW

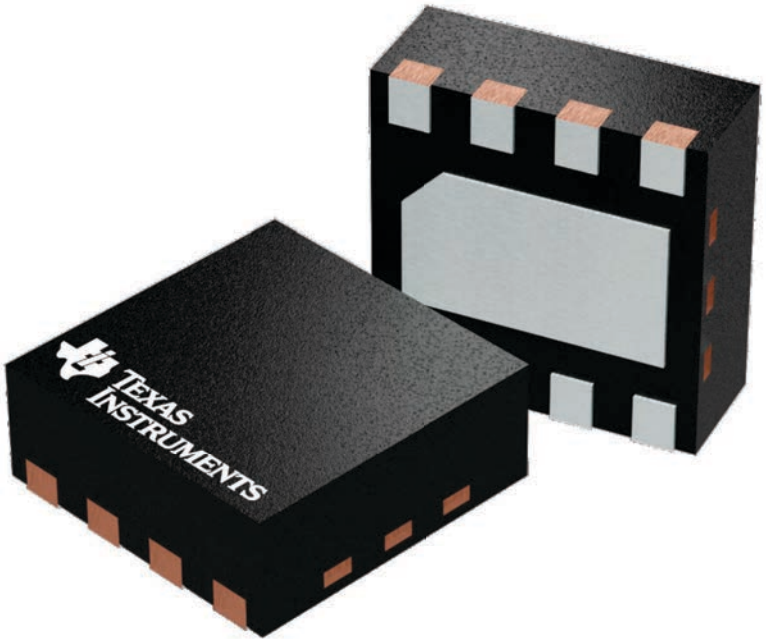
DSG 8

WSON - 0.8 mm max height

2 x 2, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



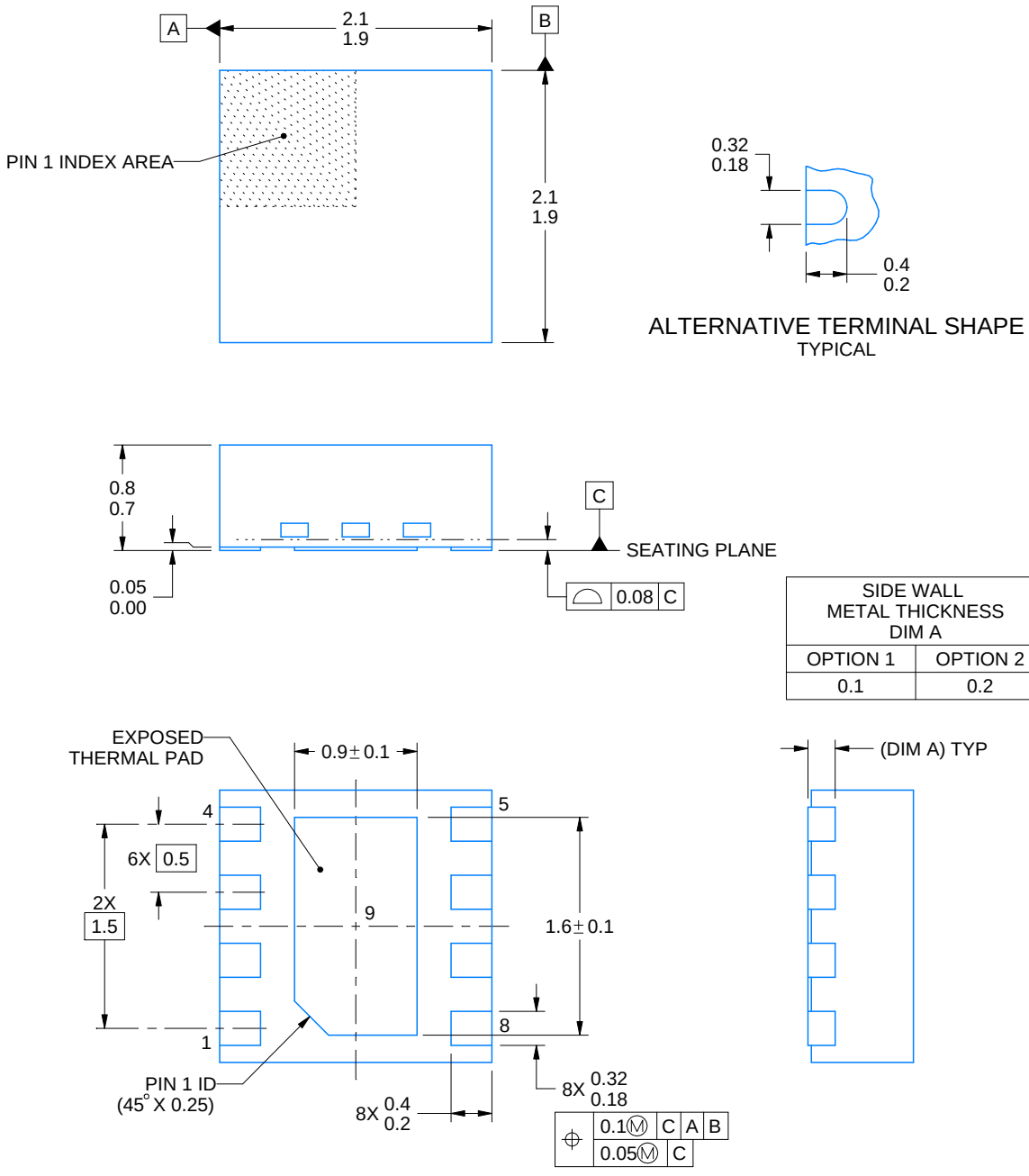
4224783/A

PACKAGE OUTLINE

DSG0008A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



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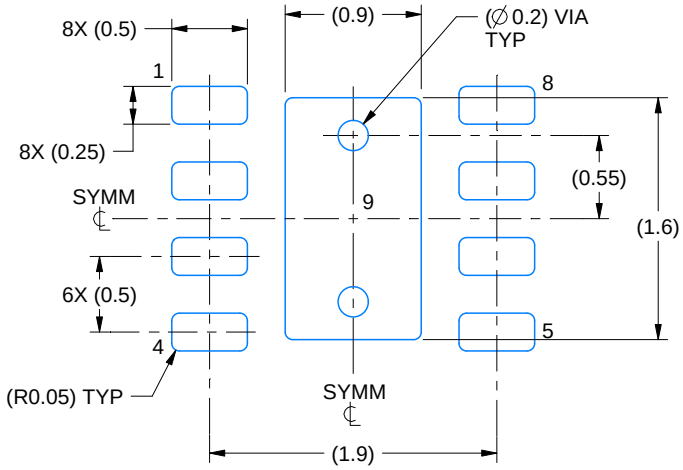
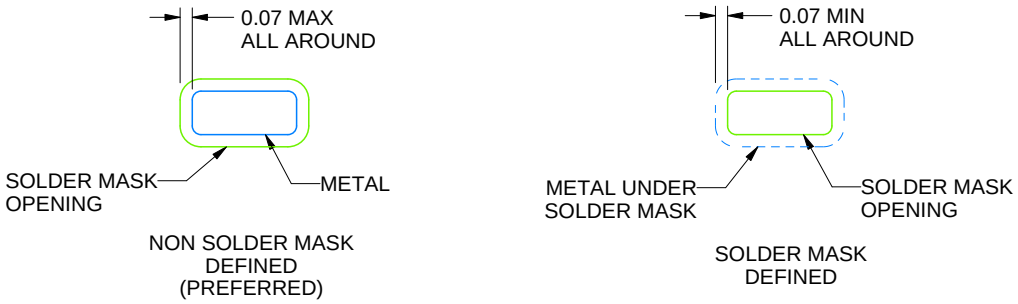
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
SCALE:20X



SOLDER MASK DETAILS

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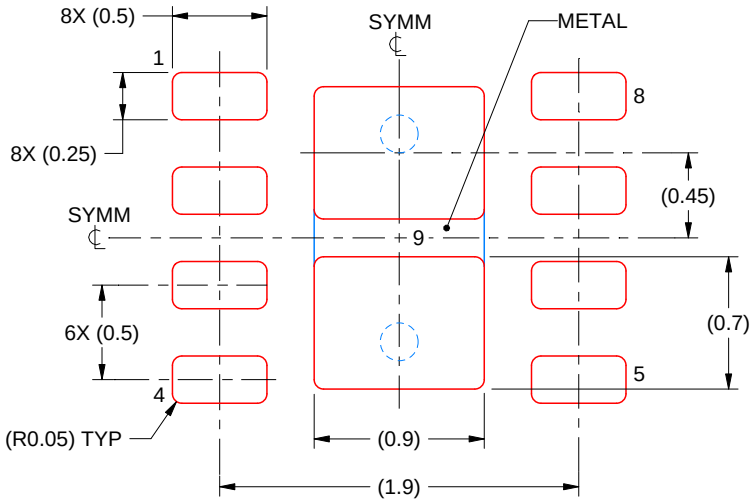
NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 9:
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要声明和免责声明

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邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265